

**Amendments to the Specification:**

Please replace paragraph [0018] with the following amended paragraph:

[0018] A photoresist material may be deposited and patterned to form a photoresist mask 310, as illustrated in FIG. 3. The photoresist material may be deposited and patterned in any conventional manner. Semiconductor device 100 may then be etched to form a fin structure 410, as illustrated in FIGS. 4A & 4B. In an exemplary implementation, silicon layer 130 may be etched in a conventional manner, with the etching terminating on buried oxide layer 120. The portion of silicon layer 130 located under photoresist mask 310 will not be etched, thereby, forming a fin structure 410 comprising silicon. In exemplary implementations, the width of fin structure ~~310~~ 410 may range from about 70 Å to about 80 Å. In one implementation, the width of fin structure ~~310~~ 410 may be approximately 75 Å.